



P-Channel 200-V (D-S) MOSFETs

PRODUCT SUMMARY				
Part Number	$V_{(BR)DSS}$ Min (V)	$r_{DS(on)}$ Max (Ω)	$V_{GS(th)}$ (V)	I_D (A)
VP2020L	-200	20 @ $V_{GS} = -4.5$ V	-0.8 to -2.5	-0.12
BSS92	-200	20 @ $V_{GS} = -10$ V	-0.8 to -2.8	-0.15

FEATURES

- High-Side Switching
- Secondary Breakdown Free: -220 V
- Low On-Resistance: 11.5 Ω
- Low-Power/Voltage Driven
- Excellent Thermal Stability

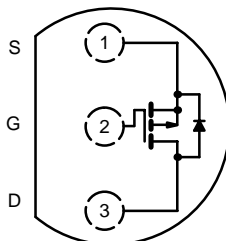
BENEFITS

- Ease in Driving Switches
- Full-Voltage Operation
- Low Offset Voltage
- Easily Driven Without Buffer
- No High-Temperature "Run-Away"

APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Power Supply, Converters
- Motor Control
- Switches

TO-226AA
(TO-92)



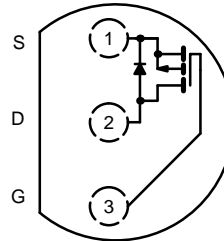
Top View
VP2020L

Device Marking
Front View



"S" = Siliconix Logo
xxxy = Date Code

TO-92-18CD
(TO-18 Lead Form)



Top View
BSS92

Device Marking
Front View



"S" = Siliconix Logo
xxxy = Date Code

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter	Symbol	VP2020L	BSS92	Unit
Drain-Source Voltage	V_{DS}	-200	-200	V
Gate-Source Voltage	V_{GS}	± 20	± 20	
Continuous Drain Current ($T_J = 150^\circ\text{C}$)	I_D	$T_A = 25^\circ\text{C}$	-0.12	A
		$T_A = 100^\circ\text{C}$	-0.08	
Pulsed Drain Current ^a	I_{DM}	-0.48	-0.6	
Power Dissipation	P_D	$T_A = 25^\circ\text{C}$	0.8	W
		$T_A = 100^\circ\text{C}$	0.32	
Thermal Resistance, Junction-to-Ambient	R_{thJA}	156	125	$^\circ\text{C}/\text{W}$
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150		$^\circ\text{C}$

Notes

a. Pulse width limited by maximum junction temperature.



SPECIFICATIONS (T _A = 25 °C UNLESS OTHERWISE NOTED)								
Parameter	Symbol	Test Conditions	Typ ^a	Limits				Unit
				VP2020L		BSS92		
				Min	Max	Min	Max	
Static								
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = -10 μA		-220				V
		V _{GS} = 0 V, I _D = -250 μA	-220			-200		
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -1 mA	-1.9	-0.8	-2.5	-0.8	-2.8	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±10		±100	nA
		T _J = 125 °C			±50			
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 0.8 × V _{(BR)DSS} , V _{GS} = 0 V			-1			μA
		T _J = 125 °C			-100			
		V _{DS} = -200 V, V _{GS} = 0 V					-60	
		T _J = 125 °C					-200	
		V _{DS} = -60 V, V _{GS} = 0 V					-0.2	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = -10 V, V _{GS} = -4.5 V	-250	-100				mA
Drain-Source On-Resistance ^b	r _{DS(on)}	V _{GS} = -10 V, I _D = -0.1 A	11.5				20	Ω
		V _{GS} = -4.5 V, I _D = -0.1 A	15		20			
		T _J = 125 °C	28		40			
		V _{GS} = -4.5 V, I _D = -0.05 A	15					
		T _J = 125 °C	28					
Forward Transconductance ^b	g _{fs}	V _{DS} = -10 V, I _D = -0.1 A	170	100				mS
		V _{DS} = -25 V, I _D = -0.1 A	170			60		
Diode Forward Voltage	V _{SD}	I _S = -0.3 A, V _{GS} = 0 V	-0.9				-1.2	V
Dynamic								
Input Capacitance	C _{iSS}	V _{DS} = -25 V, V _{GS} = 0 V f = 1 MHz	30		70		130	pF
Output Capacitance	C _{oss}		10		20		30	
Reverse Transfer Capacitance	C _{rSS}		3		10		15	
Switching^c								
Turn-On Time	t _{d(on)}	V _{DD} = -25 V, R _L = 250 Ω I _D ≅ -0.1 A, V _{GEN} = -10 V R _G = 25 Ω	6		10			ns
	t _r		8		15			
Turn-Off Time	t _{d(off)}		18		30			
	t _f		17		25			

Notes

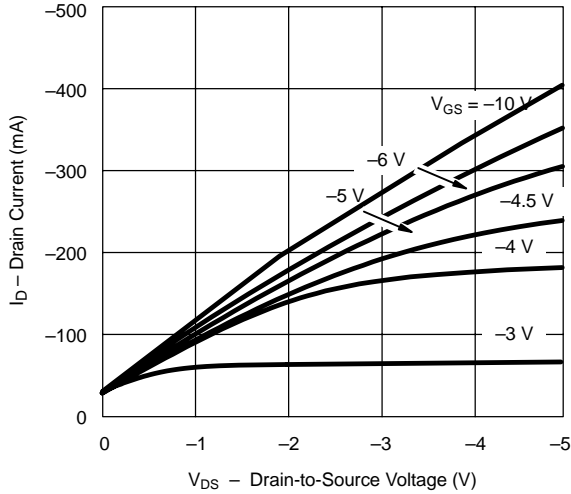
- a. For DESIGN AID ONLY, not subject to production testing.
- b. Pulse test: PW ≤ 300 μs duty cycle ≤ 2%.
- c. Switching time is essentially independent of operating temperature.

VPDQ20

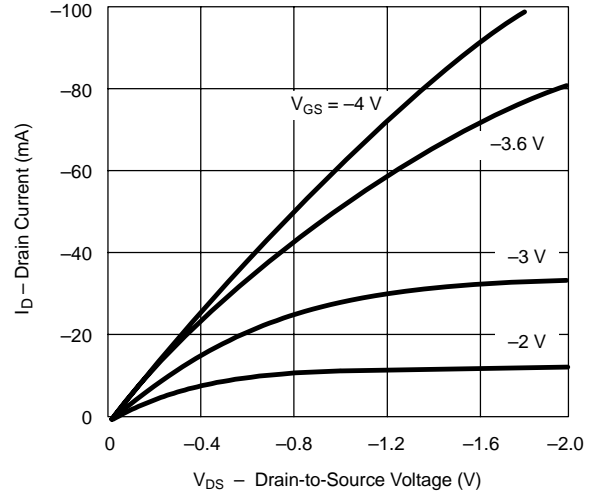


TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

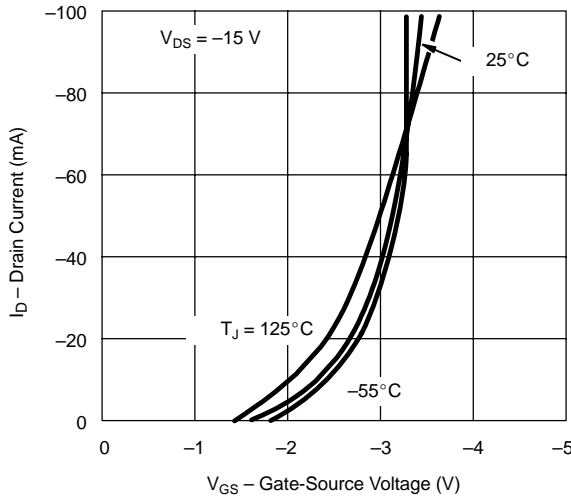
Ohmic Region Characteristics



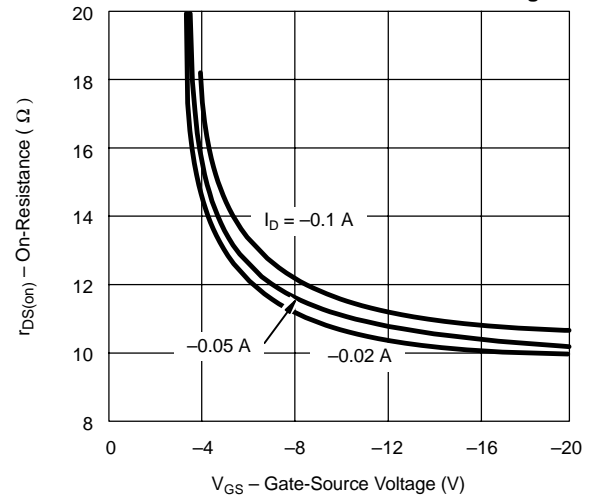
Output Characteristics for Low Gate Drive



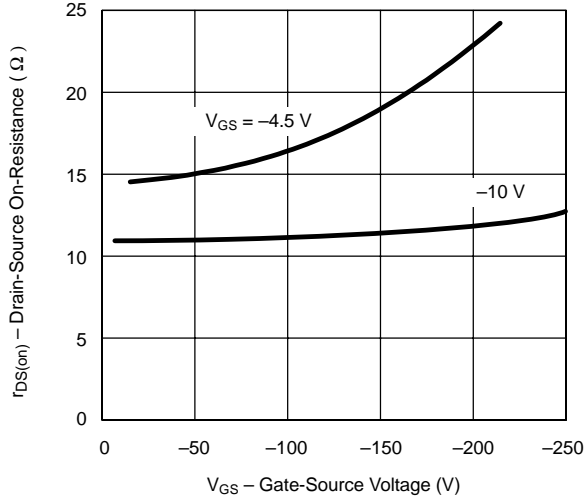
Transfer Characteristics



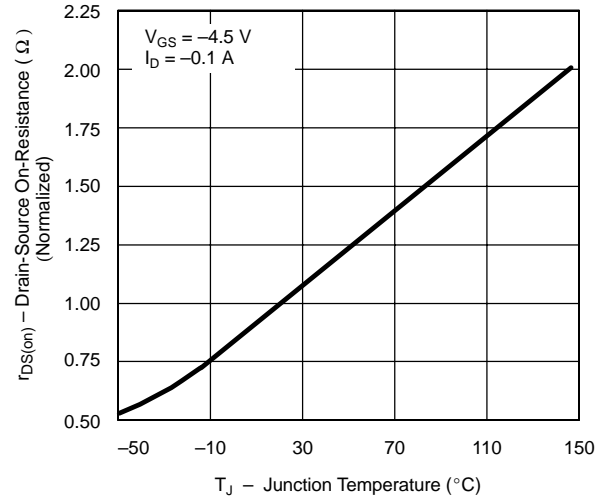
On-Resistance vs. Gate-to-Source Voltage



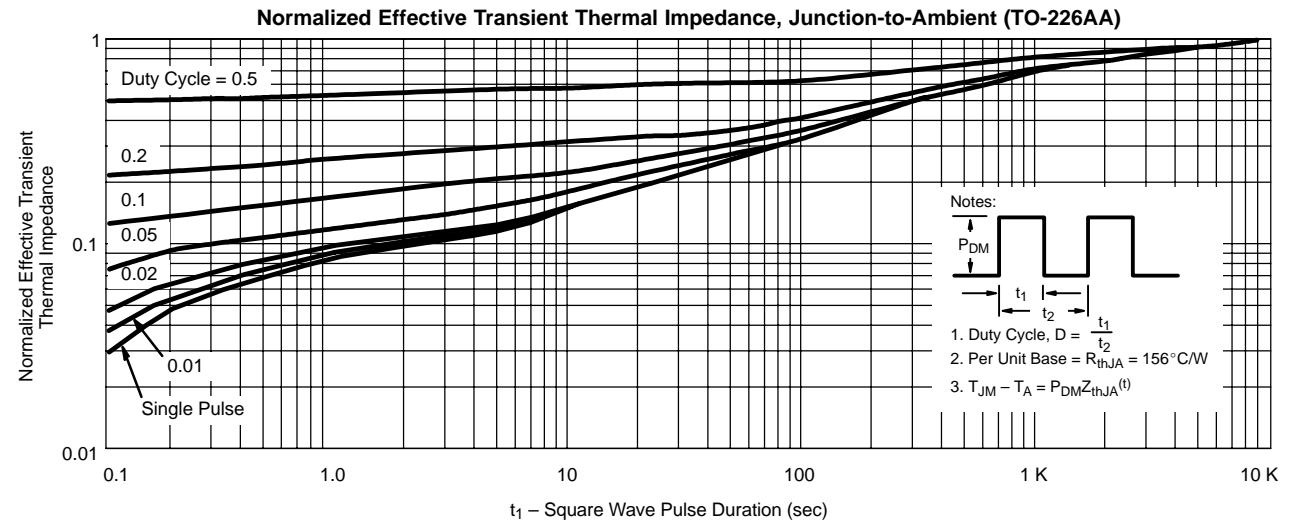
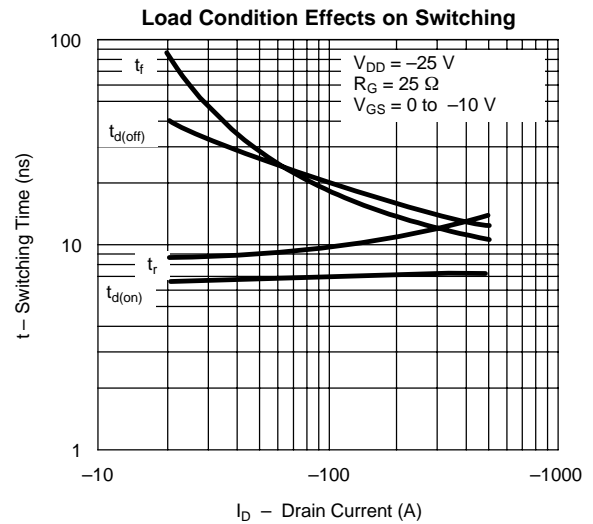
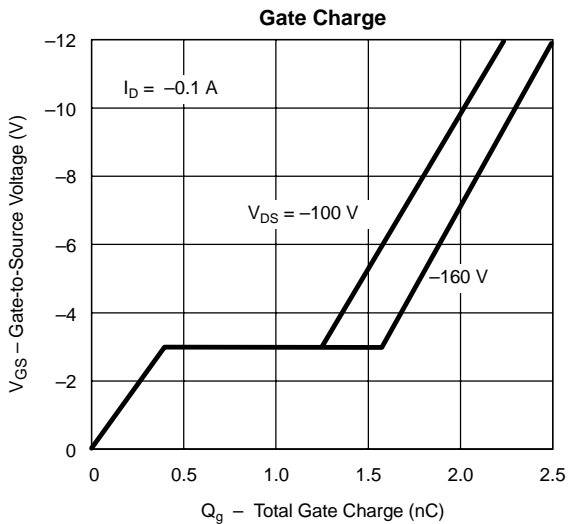
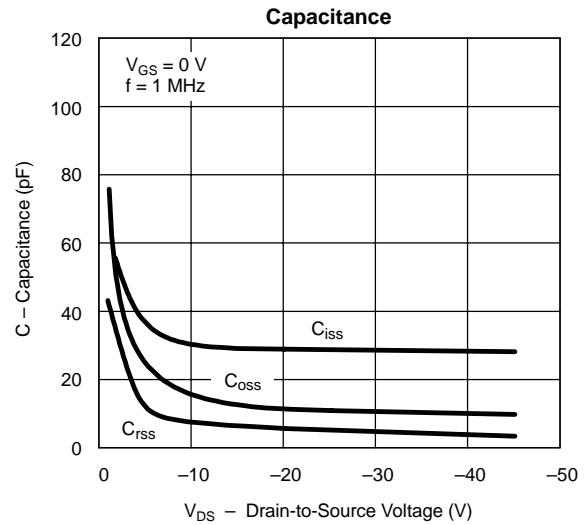
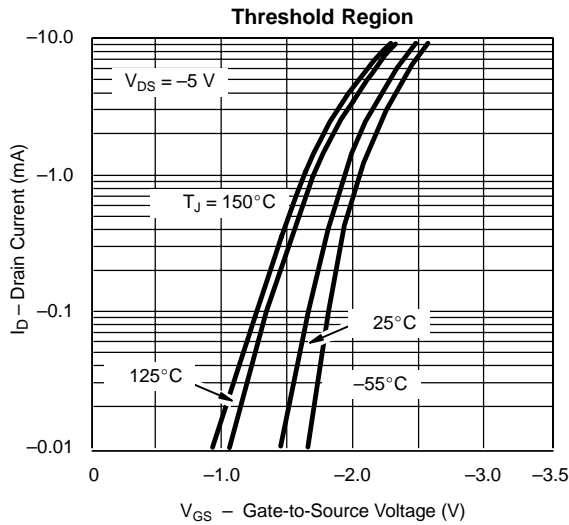
On-Resistance



Normalized On-Resistance vs. Junction Temperature



TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)





Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.